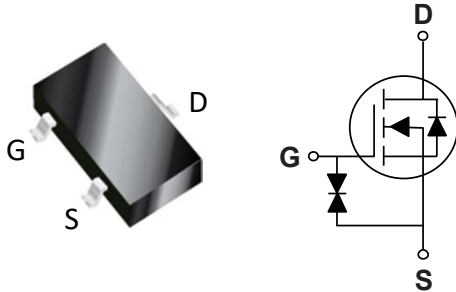




60V N-Channel MOSFETs



SOT-323

BV_{DSS}	R_{DS(ON)}	I_D
60 V	3 Ω	300 mA

Features

- $R_{DS(ON)} \leq 3\Omega @ V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-Held Instruments

Absolute Maximum Ratings T_c=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous	300	mA
I _{DM}	Drain Current - Pulsed (NOTE 1)	1.2	A
P _D	Power Dissipation	300	mW
T _J	Operating Junction Temperature Range	-55 to 150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to Ambient	417	-	°C/W



60V N-Channel MOSFETs

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V, V _{GS} =0V	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±10	uA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =500mA	---	---	3	Ω
		V _{GS} =4.5V, I _D =200mA	---	---	3.6	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.1	---	2.4	V
g _{fs}	Forward Transconductance	V _{DS} =15V, I _D =250mA	---	300	---	mS

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =5V, I _D =200mA	---	---	0.8	nC
T _{d(on)}	Delay Turn-On Time	V _{DD} =30V, R _L =150Ω, I _D =200mA , V _{GEN} =10V, R _G =10Ω	---	6	---	nS
T _{d(off)}	Delay Turn-Off Time		---	13	---	
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	---	35	pF
C _{OSS}	Output Capacitance		---	---	12	
C _{rSS}	Reverse Transfer Capacitance		---	---	7	

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current		---	---	300	mA
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =200mA	---	---	1.2	V

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.



60V N-Channel MOSFETs

Characteristics Curves

FIG. 1-Breakdown Voltage VS. Junction Temperature

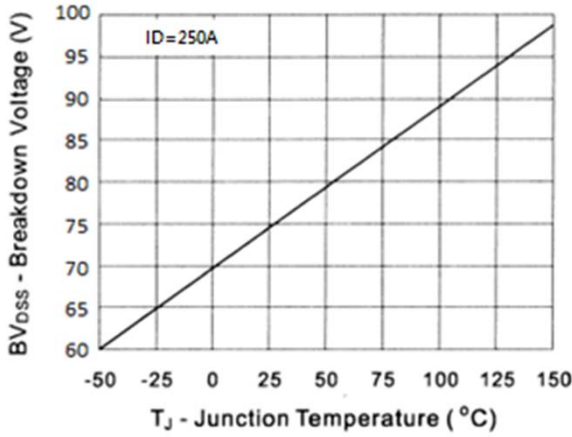


FIG. 2-On-Resistance VS. Junction Temperature

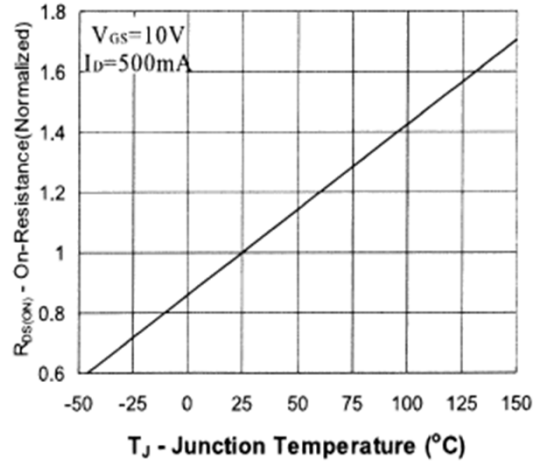


FIG. 3-On-Resistance VS. Drain Current

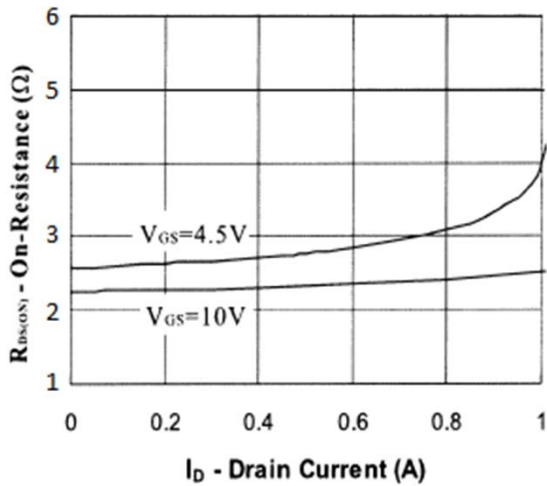


FIG. 4-On-Resistance VS. Gate-Source voltage

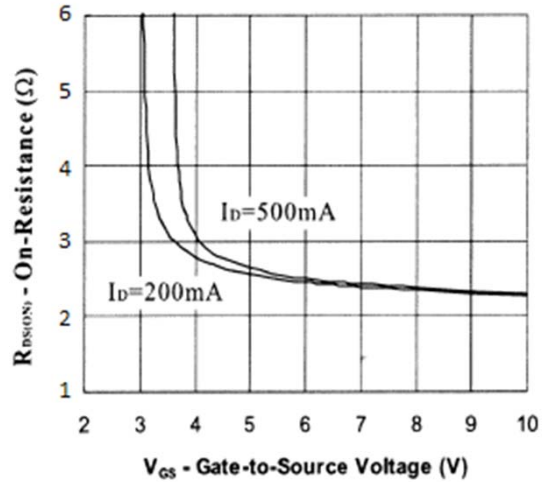


FIG. 5-Gate Charge Waveform

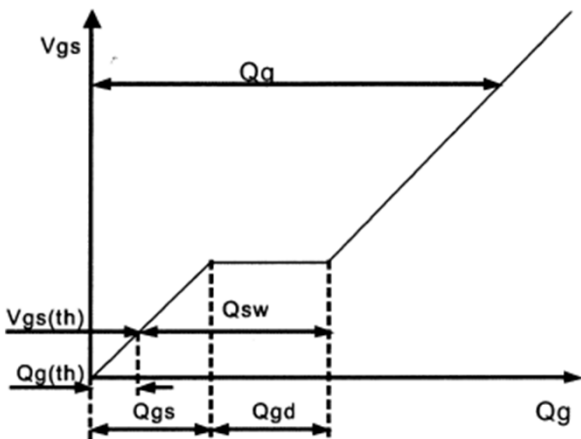
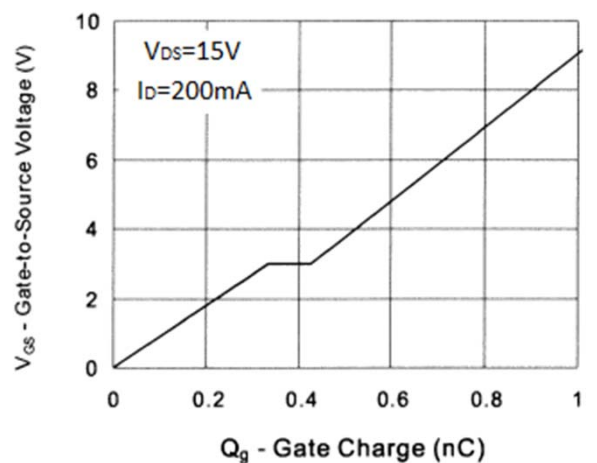


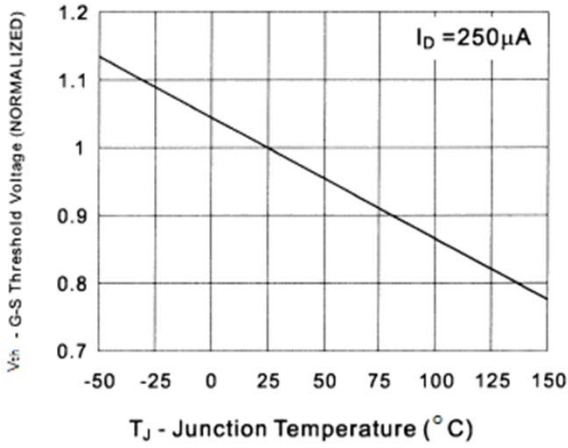
FIG. 6-Gate Charge



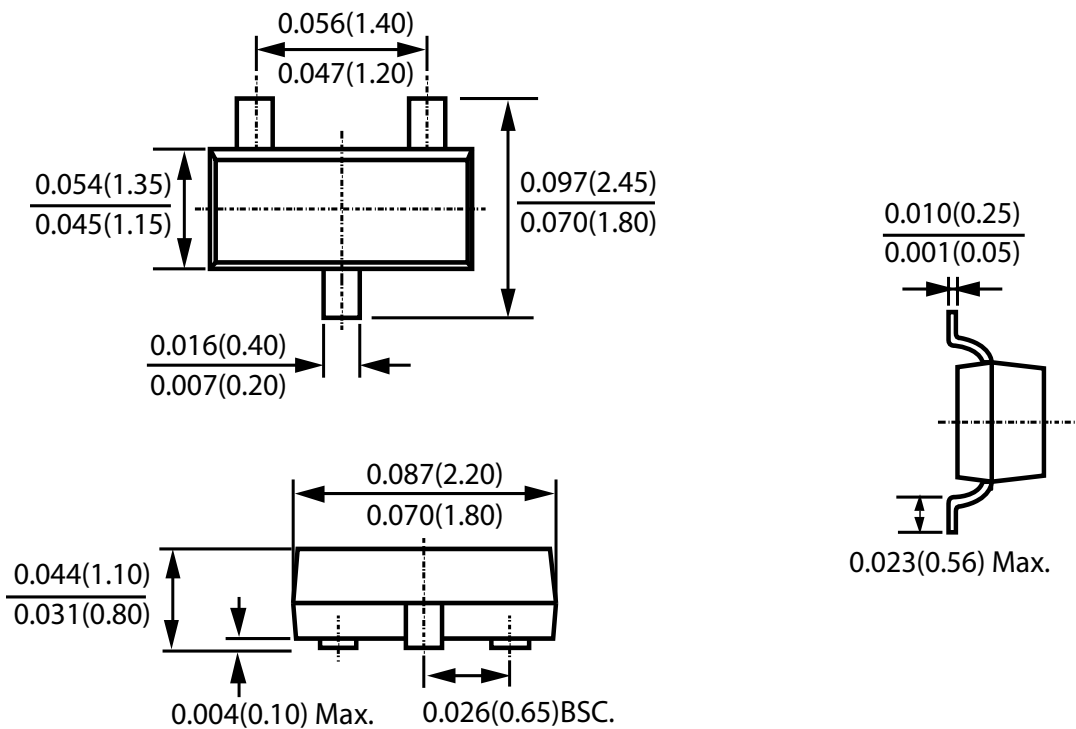


Characteristics Curves

FIG. 7-Threshold Voltage VS. Temperature



Package Outline Dimensions



SOT-323

Dimensions in inches and (millimeters)



LEGAL DISCLAIMER

- The product is provided “AS IS” without any guarantees or warranty. In association with the product, Eris Technology Corporation, its affiliates, and their directors, officers, employees, agents, successors and assigns (collectively, the “Eris”) makes no warranties of any kind, either express or implied, including but not limited to warranties of merchantability, fitness for a particular purpose, of title, or of non-infringement of third party rights.
- The information in this document and any product described herein are subject to change without notice and should not be construed as a commitment by Eris. Eris assumes no responsibility for any errors that may appear in this document.
- Eris does not assume any liability arising out of the application or use of this document or any product described herein, any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Eris and all the companies whose products are represented on Eris website, harmless against all damages.
- No license, express or implied, by estoppels or otherwise, to any intellectual property is granted by this document or by any conduct of Eris. Product name and markings notes herein may be trademarks of their respective owners.
- Eris does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- Should Customers purchase or use Eris products for any unintended or unauthorized application, Customers shall indemnify and hold Eris and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.
- The official text is written in English and the English version of this document is the only version endorsed by Eris. Any discrepancies or differences created in the translations are not binding and have no legal effect on Eris for compliance or enforcement purposes.